L Number	Hits	Search Text	DB	Time stamp
40	1	09/641125	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:28
41	11	"5885747"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:39
42	4588	(250/200,492.1,492.22,492.3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:40
43	2726	(electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:41
44	504	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two or compensation) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:42
45	502	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:43
46	65	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:43
47	64	((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:44
48	55	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:45
49	40	((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46
50	24	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46

51	20	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53
52	12	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47
53	2	((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3) and stor$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
54	8	((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47

55	3	`((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3)) and defect$4`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
56	3	`(((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3)) and defect$4) and control$5`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:49
57	2	`((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask)) and (location or adddress$3) and stor$3`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:52
58	1	`"5885747".PN.`	USPAT	2004/02/22 20:51
59	0	`6645676.URPN.`	USPAT	2004/02/22 20:52
60	0	`10/657429`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:52
61	30	`((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and ((second or two) near2 mask)`	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53

62		4	(((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and ((second or two) near2 mask)) and (location or adddress$3) and stor$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
63		3	(((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and ((second or two) near2 mask)) and (location or adddress$3) and stor$3) and defect$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55

L Number	Hits	Search Text	DB	Time stamp
40	1	09/641125	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:28
41	11	"5885747"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:39
42	4588	(250/200,492.1,492.22,492.3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:40
43	2726	(electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:05
44	504	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two or compensation) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:42
45	502	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:43
46	65	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:43
47	64	((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:44
48	55	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:45
49	40	((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46
50	24	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:46

51	20	((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53
52	12	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47
53	2	((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3) and stor$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
54	8	((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:47

55	3	(((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3)) and defect$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:55
56	3	(((((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and film) and (((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask))) and (location or adddress$3)) and defect$4) and control$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:49
57	2	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and (second near2 mask)) and (location or adddress$3) and stor$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:52
58	1	"5885747".PN.	USPAT	2004/02/22 20:51
59	0	6645676.URPN.	USPAT	2004/02/22 20:52
60	0	10/657429	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:52
61	30	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and ((second or two) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:53

62	4	((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and ((second or two) near2 mask)) and (location or adddress$3) and stor$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:01
63	3	(((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((plurality or multiple or two) near2 mask)) and (compensat$5 near2 mask)) and pattern$4) and (wafer or substrate or semiconductor) and (resist or photoresist)) and ((electron near2 optic$4) or lens)) and ((second or two) near2 mask)) and (location or adddress$3) and stor$3) and defect$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:58
64	133	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((250/200,492.1,492.22,492.3).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:58
65	133	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:58
66	6	((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage) and (main near expos$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:59
67	0	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage) and (main near expos$5)) and compensat$5 near2 mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:59
68	0	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and ((250/200,492.1,492.22,492.3).CCLS.)) and mask and stage) and (main near expos$5)) and (compensat$5 near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 20:59
69	46	((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:00
70	20	(((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)) and defect$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:01
71	18	((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)) and defect$5) and lens	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:01
72	8	(((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)) and defect$5) and lens) and (location or adddress$3) and stor$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:03

73		8	((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)) and defect$5) and lens) and (location or adddress$3) and stor$3) and (resist or film or photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:03
74		8	((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)) and defect$5) and lens) and (location or adddress$3) and stor$3) and (resist or film or photoresist)) and ((plurality or several or two or multiple) near2 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:04
75		8	(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage and compensat$5) and (main near expos$5)) and defect$5) and lens) and (location or adddress$3) and stor$3) and (resist or film or photoresist)) and ((plurality or several or two or multiple) near2 mask)) and ((electron or charged-particle or (charged adj particle)) near beam) and exposure and mask and stage and compensat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 21:05